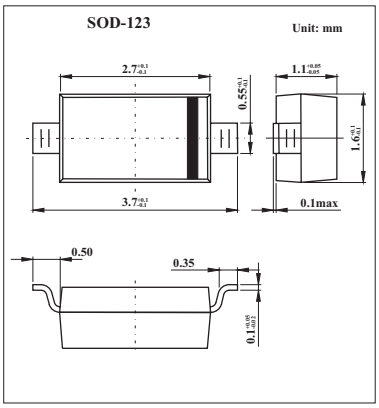
Silicon Epitaxial Planar Pin Diode

HVD142



■ Features

- Low capacitance. (C = 0.35 pF max)
- Low forward resistance. (rf=1.5 Ω max)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	V_R = 30 V			0.1	μA
Forward voltage	V_F	I_F = 10 mA			1.0	V
Capacitance	C	V_R = 1 V, f = 1 MHz			0.35	pF
Forward resistance	rf	I_F = 10 mA, f = 100 MHz			1.5	Ω
ESD-Capability *1		C = 200 pF, R = 0 Ω , Both forward reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; I_R > 100 nA at V_R =30 V

■ Marking

Marking	T2